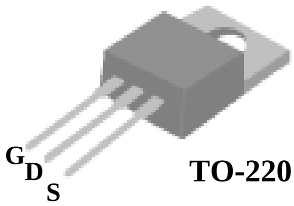
AP02N90P

Pb Free Plating Product

Advanced Power Electronics Corp.

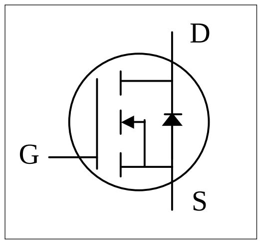
N-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ **Simple Drive Requirement**
- ▼ **Low On-resistance**
- ▼ **Fast Switching Characteristics**



TO-220

BV_{DSS}	900V
$R_{DS(ON)}$	7.2Ω
I_D	1.9A



Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications. The device is suited for DC-DC ,AC-DC converters for power applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	900	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	1.9	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	1.2	A
I_{DM}	Pulsed Drain Current[1]	6	A
P_D@T_C=25℃	Total Power Dissipation	62.5	W
	Linear Derating Factor	0.5	W/℃
E_{AS}	Single Pulse Avalanche Energy[2]	18	mJ
I_{AR}	Avalanche Current	1.9	A
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter		Value	Units
Rthj-c	Thermal Resistance Junction-case	Max.	2.0	℃/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	62	℃/W

Electrical Characteristics@T_j=25^{o}C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=1mA	900	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=1mA	-	0.8	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=0.85A	-	-	7.2	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	2	-	4	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=1.9A	-	2	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25^{o}C)	V_{DS}=900V, V_{GS}=0V	-	-	10	uA
	Drain-Source Leakage Current (T_j=125^{o}C)	V_{DS}=720V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±30V	-	-	±100	nA
Q_g	Total Gate Charge[3]	I_D=1.9A	-	12	20	nC
Q_{gs}	Gate-Source Charge	V_{DS}=540V	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=10V	-	4.7	-	nC
$t_{d(on)}$	Turn-on Delay Time[3]	V_{DD}=450V	-	10	-	ns
t_r	Rise Time	I_D=1.9A	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=10Ω,V_{GS}=10V	-	18	-	ns
t_f	Fall Time	R_D=236Ω	-	9	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	630	1000	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	40	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	4	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[3]	I_S=1.9A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_S=1.9A, V_{GS}=0V,	-	360	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/µs	-	1.8	-	µC

Notes:

1.Pulse width limited by safe operating area.

2.Starting T_j=25^{o}C , V_{DD}=50V , L=10mH , R_G=25Ω , I_{AS}=1.9A.

3.Pulse width $\leq$300us , duty cycle $\leq$2%.

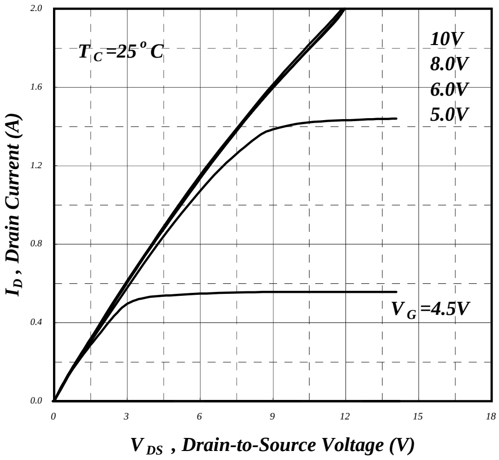


Fig 1. Typical Output Characteristics

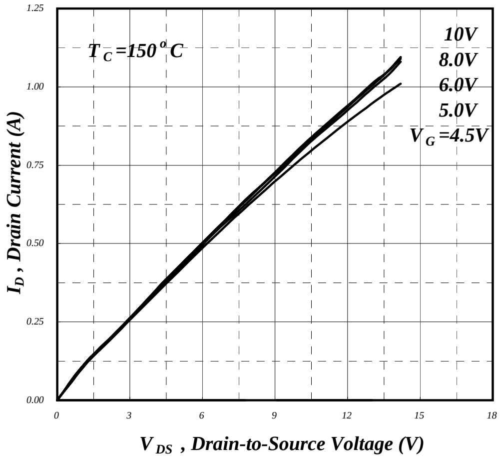


Fig 2. Typical Output Characteristics

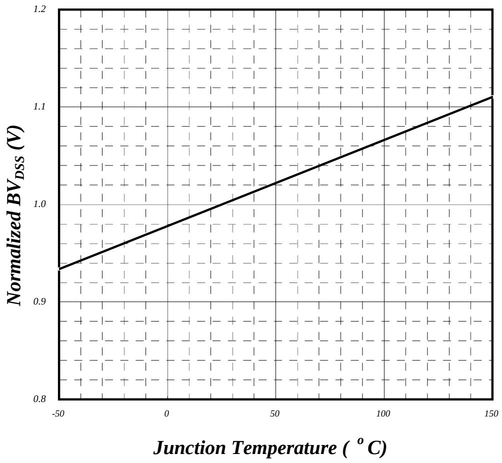


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

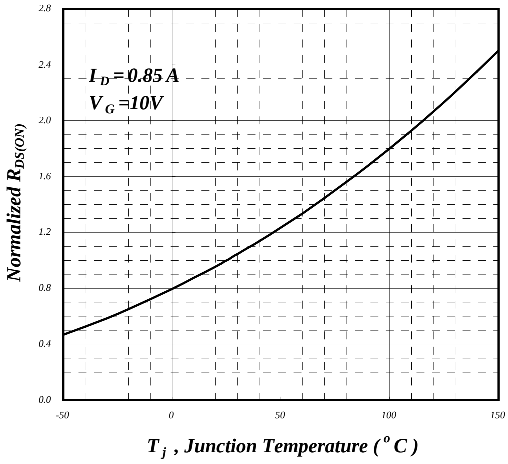


Fig 4. Normalized On-Resistance v.s. Junction Temperature

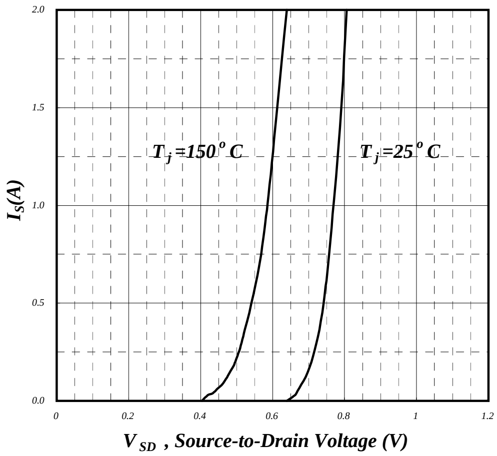


Fig 5. Forward Characteristic of Reverse Diode

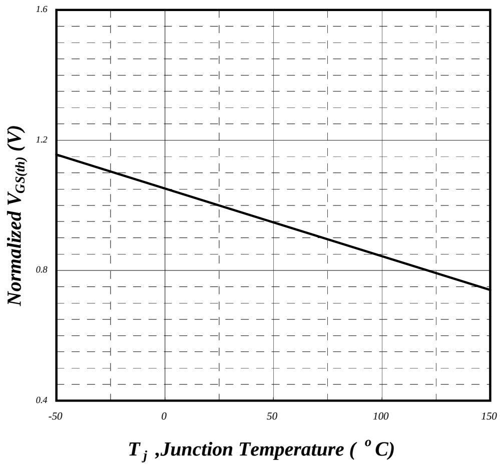


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

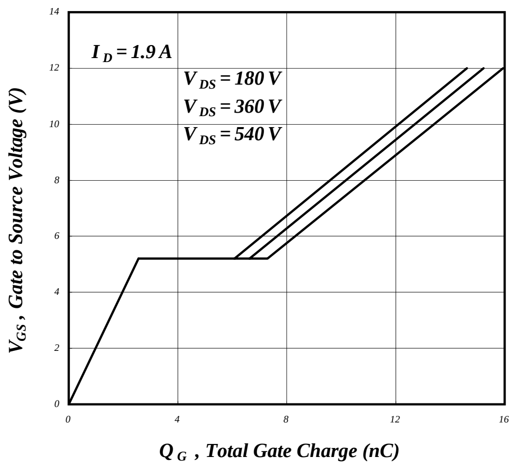


Fig 7. Gate Charge Characteristics

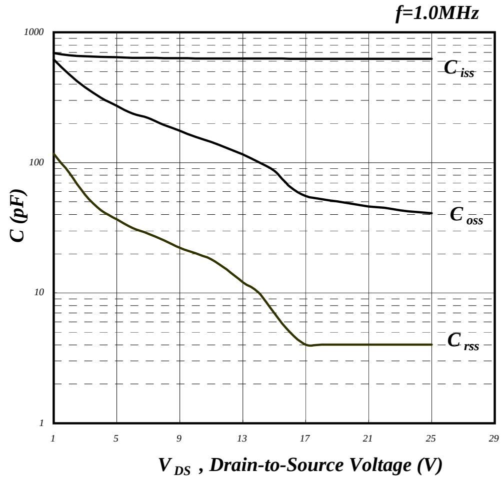


Fig 8. Typical Capacitance Characteristics

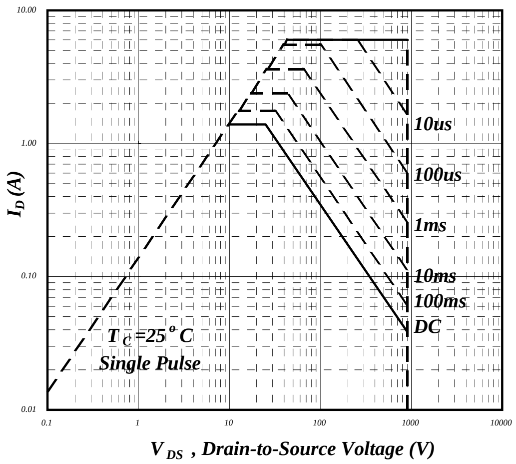


Fig 9. Maximum Safe Operating Area

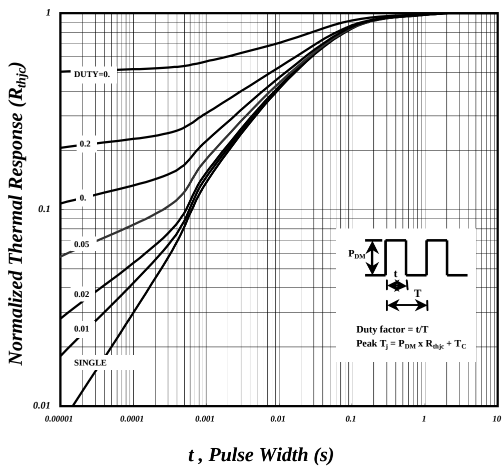


Fig 10. Effective Transient Thermal Impedance

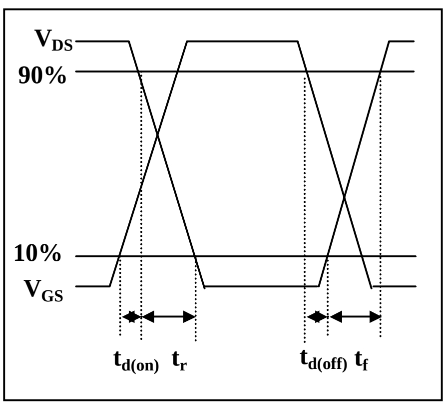


Fig 11. Switching Time Waveform

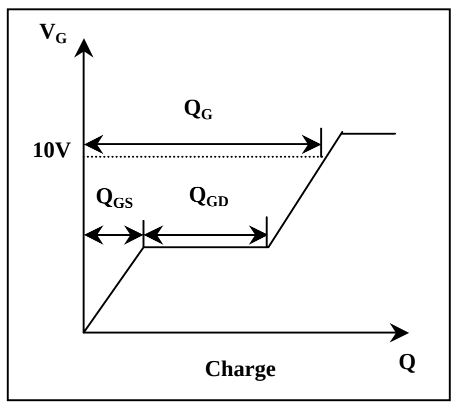


Fig 12. Gate Charge Waveform